# **DMG264H0**

# Silicon NPN epitaxial planar type (Tr1) Silicon PNP epitaxial planar type (Tr2)

For digital circuits

## ■ Features

- ullet Low collector-emitter saturation voltage  $V_{\text{CE(sat)}}$
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

# ■ Basic Part Number

DRC2144E + DRA2543E (Individual)

# ■ Packaging

Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

## ■ Absolute Maximum Ratings $T_a = 25$ °C

	Parameter	Symbol	Rating	Unit
Tr1	Collector-base voltage (Emitter open)	V <sub>CBO</sub>	50	V
	Collector-emitter voltage (Base open)	V <sub>CEO</sub>	50	V
	Collector current	$I_{C}$	100	mA
Tr2	Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-50	V
	Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-50	V
	Collector current	$I_{C}$	-500	mA
Overall	Total power dissipation	P <sub>T</sub>	300	mW
	Junction temperature	T <sub>j</sub>	150	°C
	Storage temperature	T <sub>stg</sub>	-55 to +150	°C

# ■ Package

Code

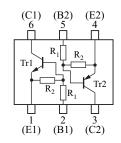
Mini6-G4-B

Pin Name

1: Emitter (Tr1) 4: Emitter (Tr2) 2: Base (Tr1) 5: Base (Tr2) 3: Collecter (Tr2) 6: Collecter (Tr1)

## ■ Marking Symbol: T0

## ■ Internal Connection



	Tr1	$R_1$	47	kΩ	
Resistance		R <sub>2</sub>	47		
value	Tr2	$R_1$	4.7	1:0	
		R <sub>2</sub>	4.7	kΩ	

# ■ Electrical Characteristics $T_a = 25$ °C±3°C

## • Tr1

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_C = 10 \mu A, I_E = 0$	50			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = 2 \text{ mA}, I_B = 0$	50			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = 50 \text{ V}, I_{E} = 0$			0.1	μA
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = 50 \text{ V}, I_{B} = 0$			0.5	μΑ
Emitter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{EB} = 6 \text{ V}, I_{C} = 0$			0.1	mA
Forward current transfer ratio	h <sub>FE</sub>	$V_{CE} = 10 \text{ V}, I_{C} = 5 \text{ mA}$	80			_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$			0.25	V
Input voltage (ON)	V <sub>I(on)</sub>	$V_{CE} = 0.2 \text{ V}, I_{C} = 5 \text{ mA}$	3.6			V
Input voltage (OFF)	V <sub>I(off)</sub>	$V_{CE} = 5 \text{ V}, I_{C} = 100 \mu\text{A}$			0.8	V
Input resistance	R <sub>1</sub>		-30%	47	+30%	kΩ
Resistance ratio	$R_1/R_2$		0.8	1.0	1.2	_

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

**Panasonic** 

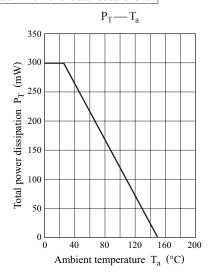
# ■ Electrical Characteristics (Continued) $T_a = 25$ °C±3°C

## • Tr2

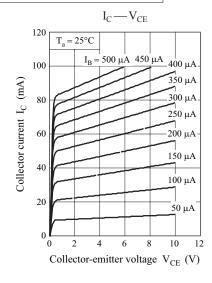
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_{\rm C} = -10  \mu \text{A}, I_{\rm E} = 0$	-50			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{\rm CB} = -50 \text{ V}, I_{\rm E} = 0$			-1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = -50 \text{ V}, I_{B} = 0$			-1	μΑ
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = -6 \text{ V}, I_C = 0$			-2	mA
Forward current transfer ratio	$h_{\mathrm{FE}}$	$V_{CE} = -10 \text{ V}, I_{C} = -100 \text{ mA}$	50			_
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = -100 \text{ mA}, I_B = -5 \text{ mA}$			-0.25	V
Input voltage (ON)	V <sub>I(on)</sub>	$V_{CE} = -0.2 \text{ V}, I_{C} = -50 \text{ mA}$	-3.6			V
Input voltage (OFF)	V <sub>I(off)</sub>	$V_{CE} = -5 \text{ V}, I_{C} = -100 \mu\text{A}$			-0.7	V
Input resistance	$R_1$		-30%	4.7	+30%	kΩ
Resistance ratio	$R_1/R_2$		0.8	1.0	1.2	_

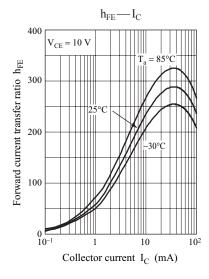
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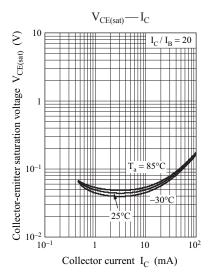
# Common characteristics chart



# Characteristics charts of Tr1

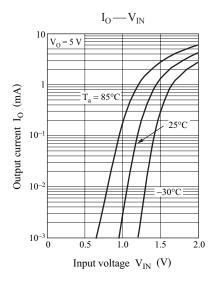


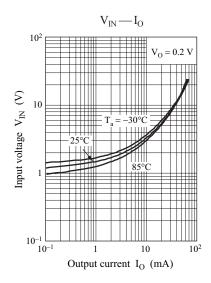




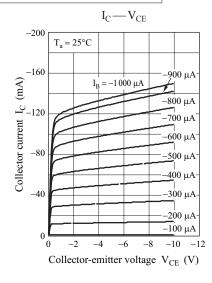
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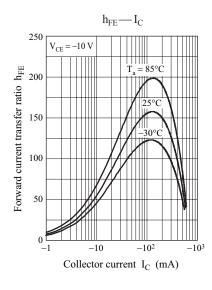
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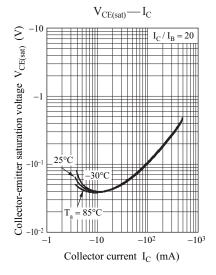


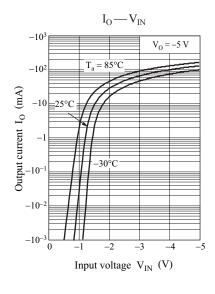


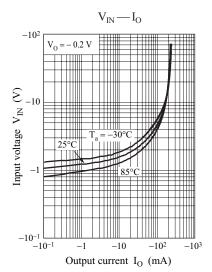
# Characteristics charts of Tr2



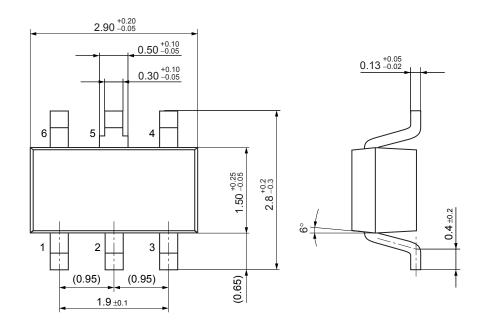


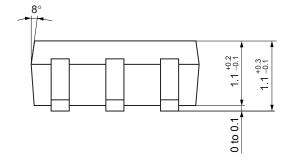






Mini6-G4-B Unit: mm





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